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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Shashank Sharma and)

Mahendra Kumar Sunkara)

#5

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Serial No:

09/896,834

For:

LOW TEMPERATURE SYNTHESIS OF

SEMICONDUCTOR FIBERS

Atty. Docket No.: AD138/2001

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Yelizaveta Klimova Troxler
(Typed or Printed Name)
(Signature)

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Enclosed is a list and copies of references considered by Applicant to be pertinent in the examination of the above-identified patent application.

- U.S. Patent 5,725,674 by Moustakas et al. for a `Device and Method for Epitaxially Growing Gallium Nitride Layers' issued in March of 1998;
- U.S. Patent 6,051,849 by Davis et al. for a `Gallium Nitride Semiconductor Structures Including a Lateral Gallium Nitride Layer that Extends from an Underlying Gallium Nitride Layer issued in April of 2000;
- U.S. Patent 5,858,862 by Westwater for `Process for Producing Ouantum Fine Wire' issued in January of 1999';

- U.S. Patent 5,962,863 by Russell for a `Laterally Disposed Nanostructures of Silicon on an Insulating Substrate' issued in October of 1999;
- U.S. Patent 5,381,753 by Okajima for a `Fabrication Method fo Fine Structures' issued in January of 1995;
- U.S. Patent 4,886,683 by Hoke et al. for a `Low Temperature Metalorganic Chemical Vapor Depostion Growth of Group II-VI Semiconductor Materials' issued in December of 1989;
- U.S. Patent 5,334,296 by Henkens et al. for a `Peroxidase Colloidal Gold Oxidase Biosensors for Mediatoless Glucose determination' issued in August of 1994;
- U.S. Patent 6,033,866 by Guo for a `Highly Sensitive Amperometric Bi-mediator-based Glucose Biosensor' issued in March of 2000;
- U.S. Patent 5,922,183 by Rauh for a Metal Oxide Matrix Biosensors' issued in July of 1999;
- U.S. Patent 6,063,246 by Wolfe et al. for a `Method for Depositing a Carbon film on a Membrane, issued in May of 2000;

Abstract of PCT Publication W09944224A1 by Davis et al. for `Methods of Fabricating Gallium Nitride Semiconductor Layers by Lateral Overgrowth Through Masks, and Gallium Nitride Semiconductor Structures Fabricated Thereby' publication date September of 1999;

Abstract of PCT Publication W0026422A1 by Yamamura et al. for a `High Purity gallium for Preparation of Compound Semiconductor, and Method and Apparatus for Purifying the Same' published May 11, 2000;

Abstract of PCT Publication W09965068A1 by Zheleva et al. for a `Fabrication of Gallium Nitride Semiconductor Layers by Lateral Growth from Trench Sidewalls' published December of 1999;

Abstract of Japanese Patent JP 2086121A2 by Toru and Toshiyuki for a `Device for Vapor Growth Semiconductor' issued in March of 1990;

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Zhang et al., `One-dimensional growth mechanism of crystalline silicon nanowires' Journal of Crystal Growth 197 (1999) 136-140;

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Scheier et al. `Growth of silicon nanostructures on graphite' Surface Science 458 (2000) 113-122;

Yu et al. `Nanoscale Silicon Wires Synthesized Using Simple Physical Evaporation' Applied Physics Letters, Volume 72, Number 26, June 29, 1998, pp. 3458-3460, June 29, 1998;

Zhang et al. `Silicon nanowires prepared by Laser ablation at High Temperature', Applied Physics Letters', Volume 72, Number 15, pp. 1835-1837, April 13, 1998;

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Respectfully submitted,

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Reg. No. 35,475

ATTORNEY'S DOCKET NO. LIST OF PRIOR ART CITED BY APPLICANT AD138/2001 (Use several sheets if necessary) TRADES U. S. PATENT DOCUMENTS ILING DATE CLASS. NAME DOCUMENT NUMBER DATE Moustakas et al. 6743/10/98 Davis et al. 9 4/18/00 Westwater et al. 86 1/12/99 Russell et al. 8 6 3 10/5/99 Okajima et al. 1/14/95 5 Wolfe et al. 6 5/16/00 3 Hoke et al. 8 Henkens et al. 9 6 8/2/94 2 Guo et al. 6 6 3/7/00 8 Rayh 8 3 7/13/99 2 · Supply data if known. FOREIGN PATENT DOCUMENTS SUB-SHTS CLASS' NAME DATE DOUNTRY **DOCUMENT NUMBER** CLASS' Nishibe Toru etal 8 laban 3/27/90 16 YamadaTakeshi 4/4/2/99 OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.) * 70N Publication No. WO026422A1 for "HIGH PURITY GALLIUM FOR PREPARATION OF Ш COMPOUND SEMICONDUCTOR, AND METHOD AND APPARATUS FOR PURIFYING THE SAME" by Yamamura et al., published on May 11, 2000; Publication No. WO9965068A1 for "FABRICATION OF GALLIUM NITRIDE SEMICONDUCTOR LAYERS BY LATERAL GROWTH FROM TRENCH SIDEWALLS" by Zheleva et al., published on December 16, 1999; Publication No. WO9944224A1 for "METHOD OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS BY LATERAL OVERGROWTH THROUGH MASKS, AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES FABRICATED THEREBY" by Davis et al., published on September 2, 1999; Patent and Trademark Office - U.S. DEPARTMENT of COMMERCE PTO Form 3.72 (MR)

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